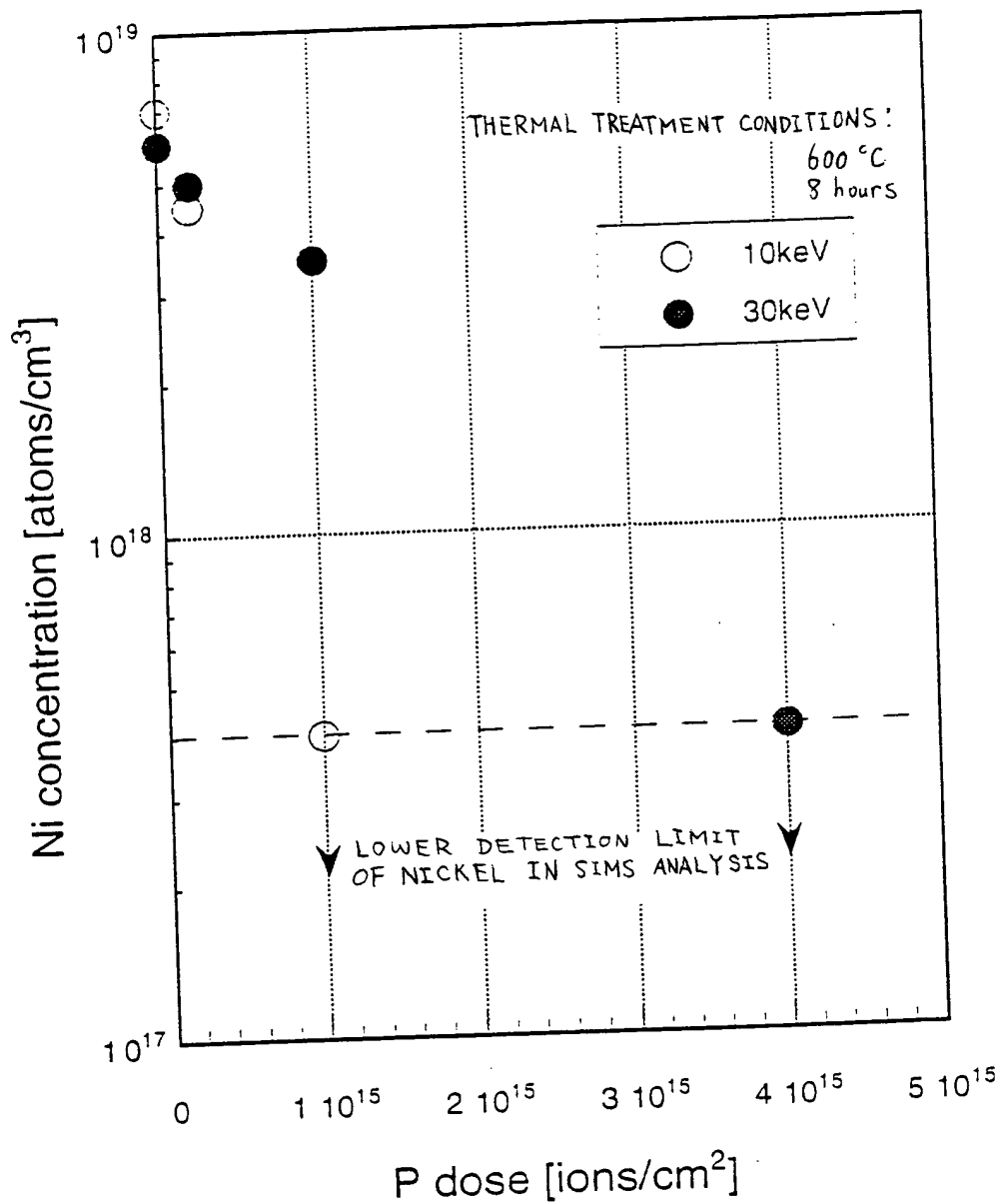


Fig. 1



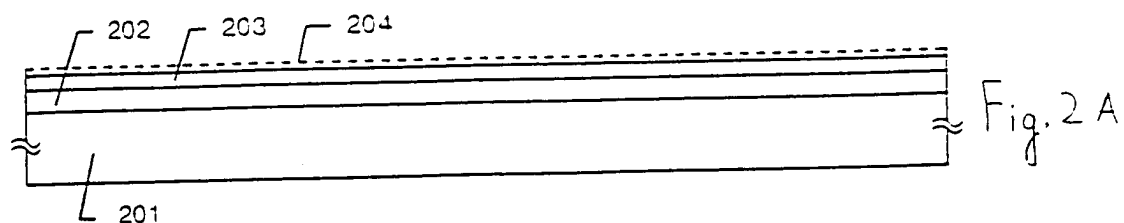


Fig. 2 A

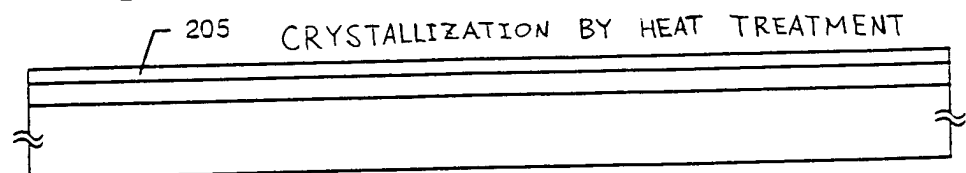


Fig. 2 B

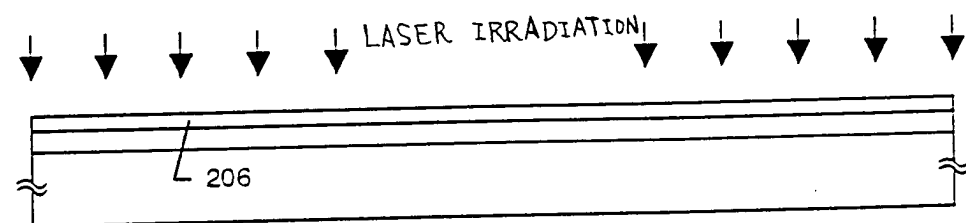


Fig. 2C

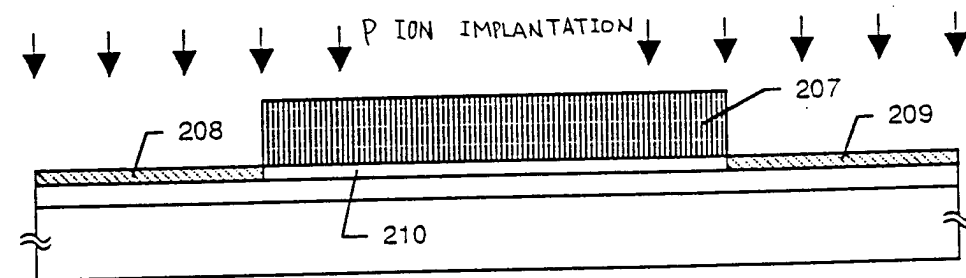


Fig. 2D

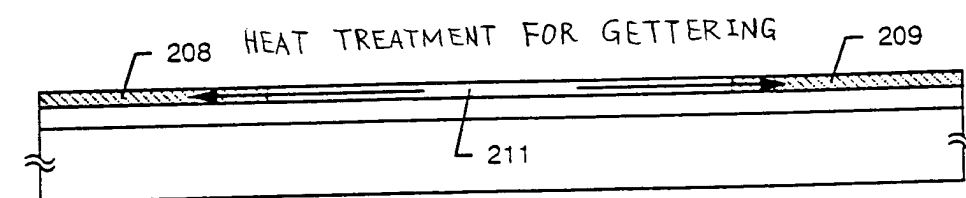


Fig. 2E

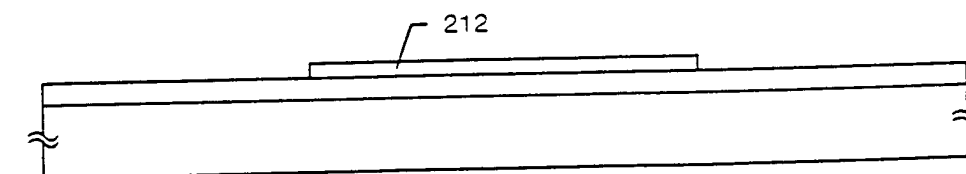


Fig. 2F

Fig. 3A



Fig. 3D



Fig. 3B

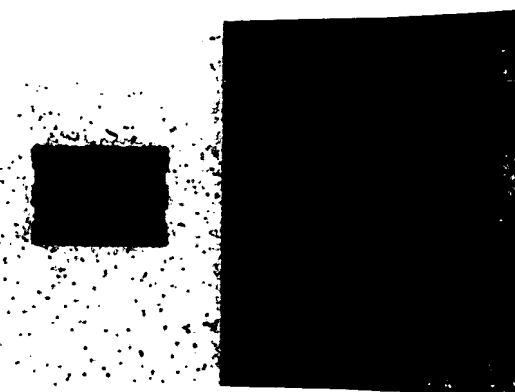


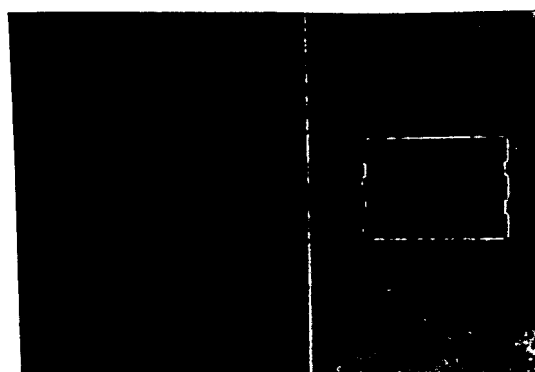
Fig. 3E



Fig. 3C



Fig. 3F



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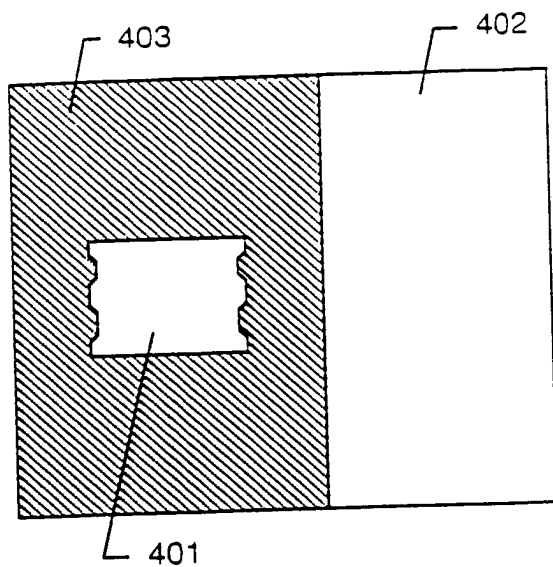


Fig. 4

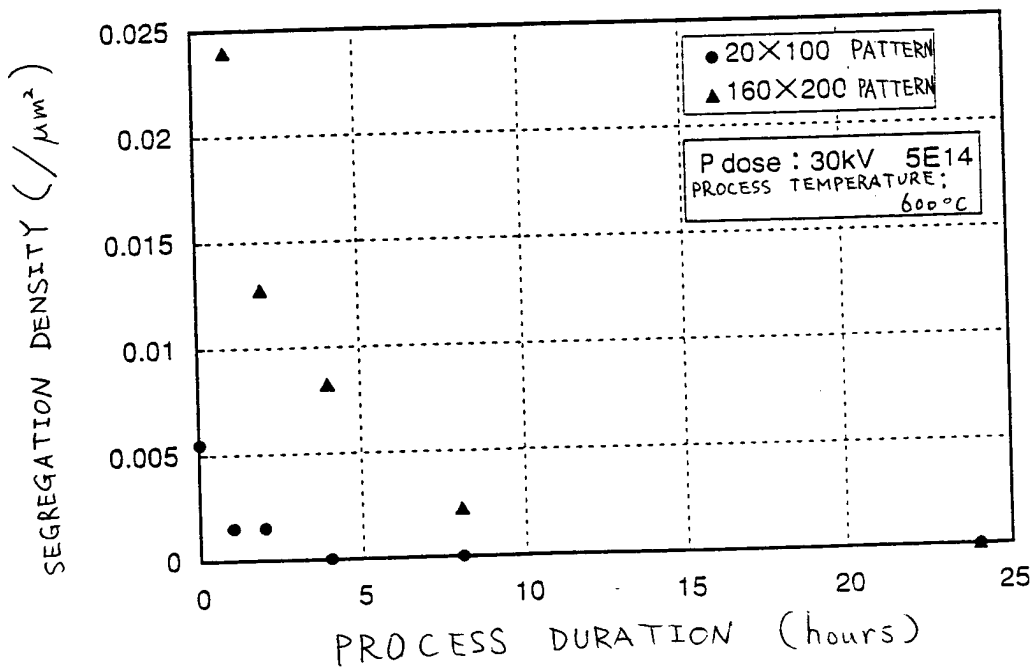


Fig. 5

Fig. 6A

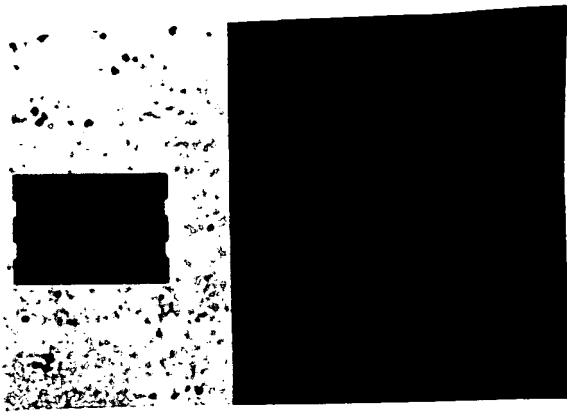


Fig. 6D

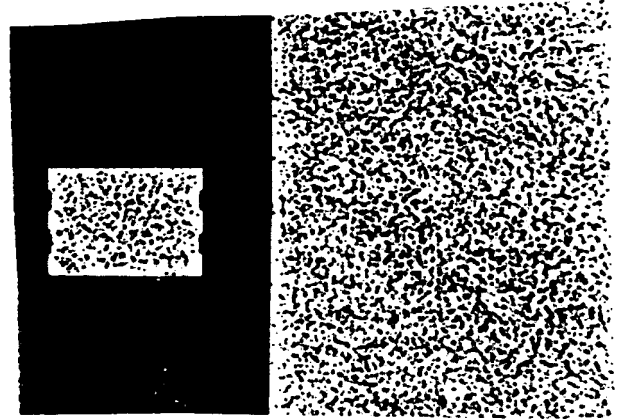


Fig. 6B

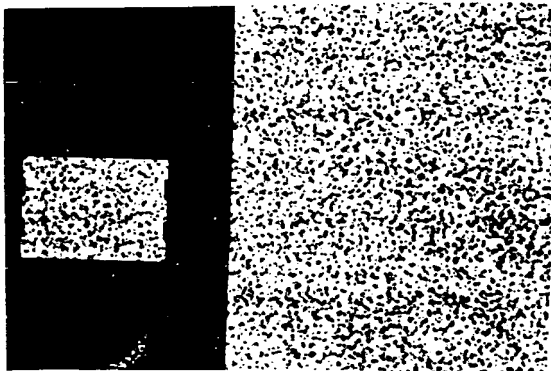


Fig. 6E

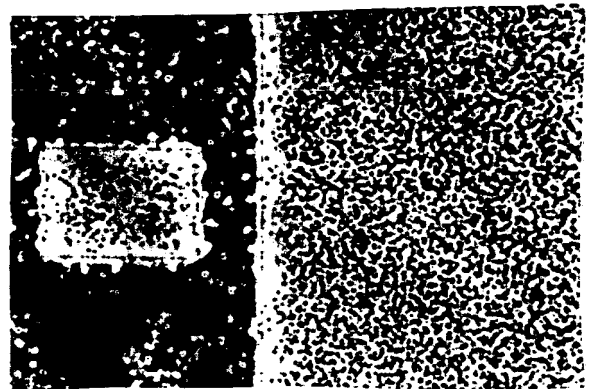


Fig. 6C

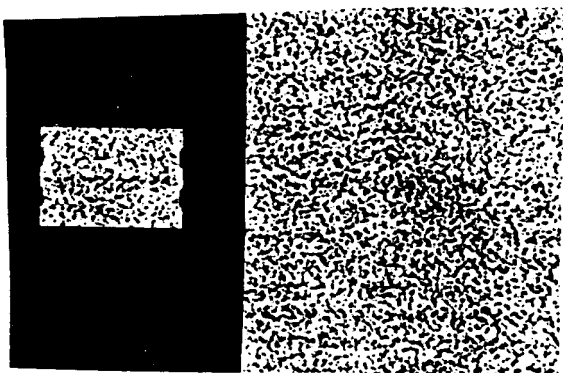


Fig. 6F



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Fig. 7

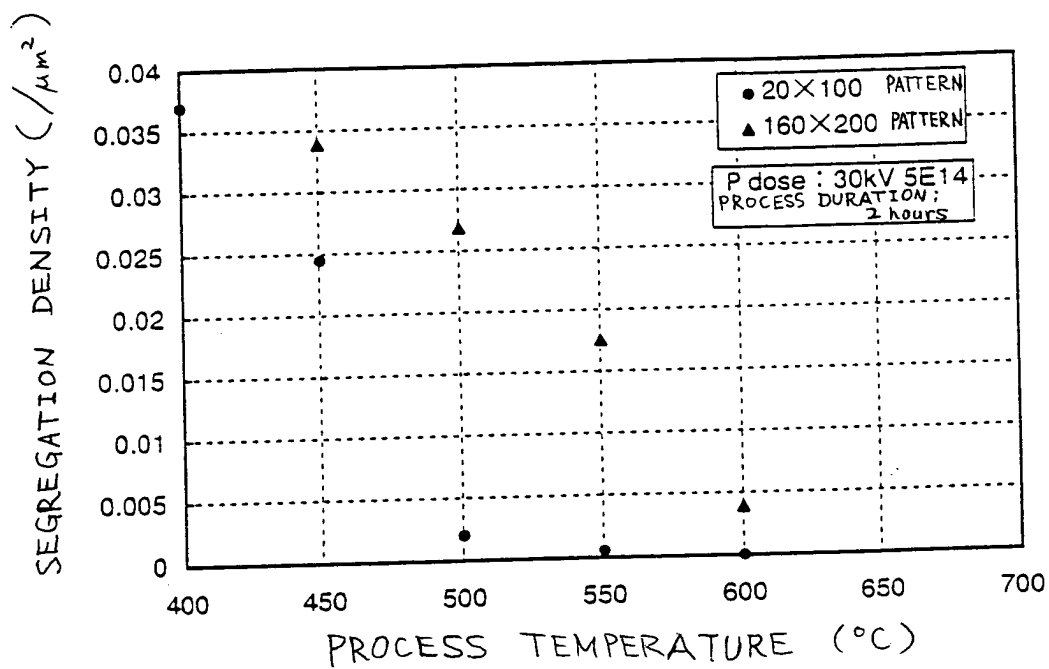


Fig. 8A

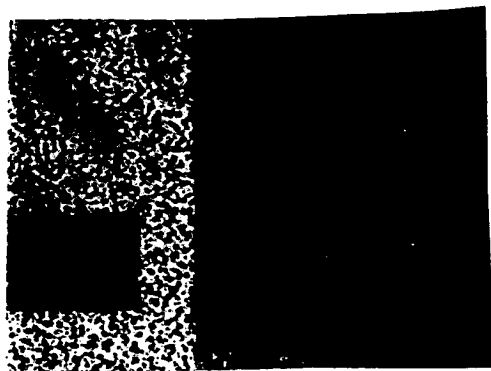


Fig. 8D

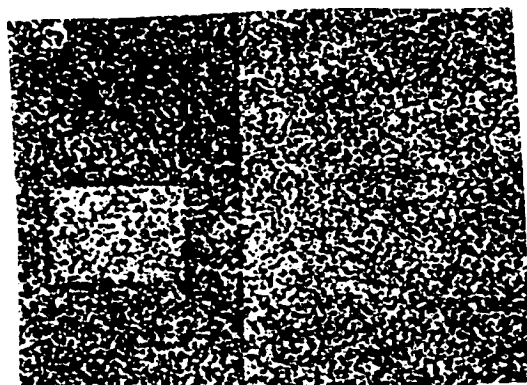


Fig. 8B

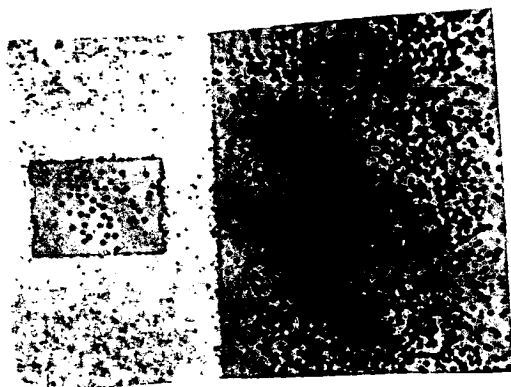


Fig. 8E



Fig. 8C

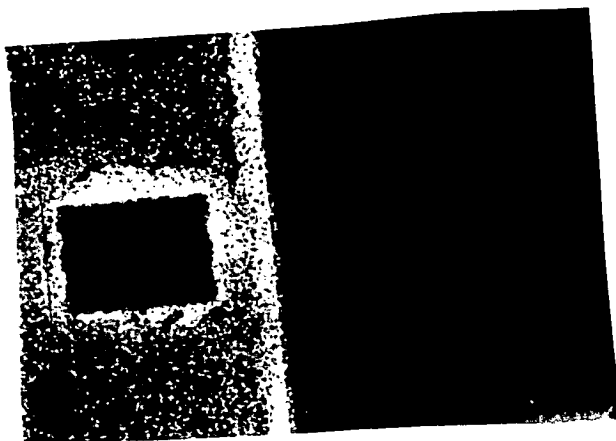
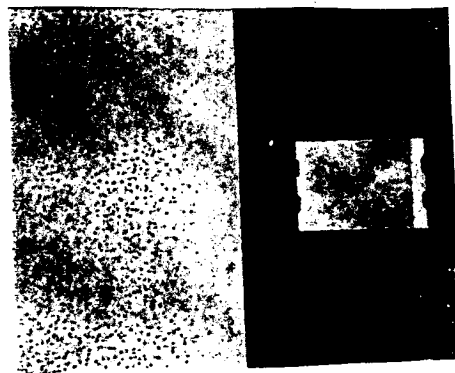


Fig. 8F



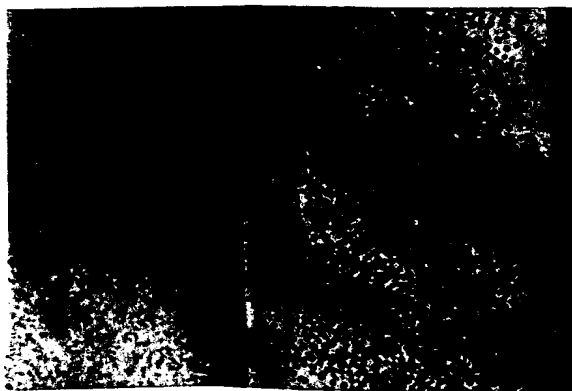


Fig. 9A

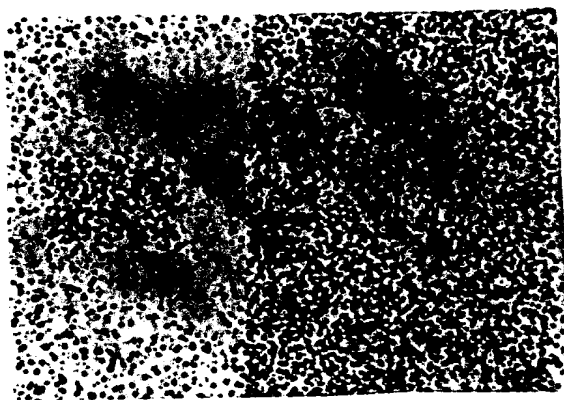
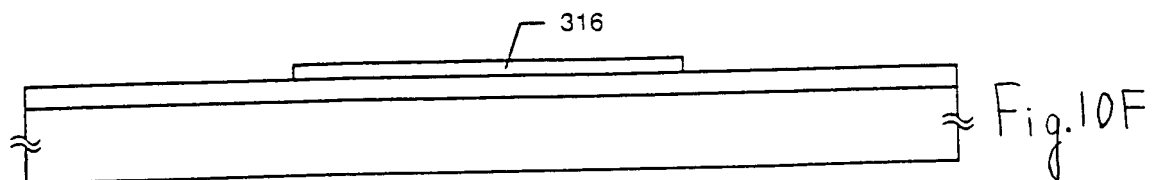
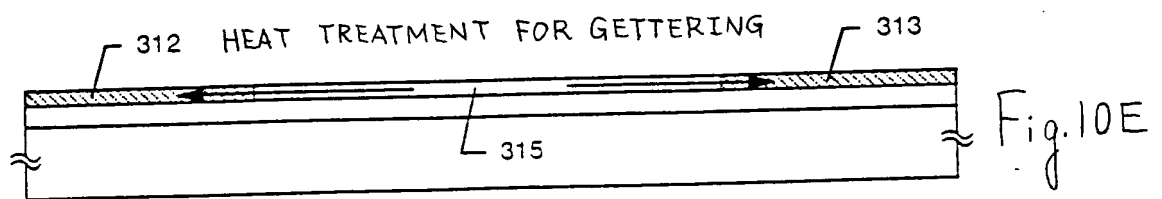
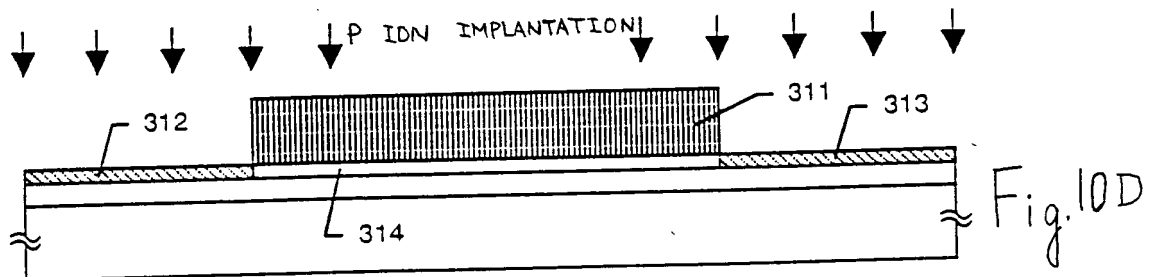
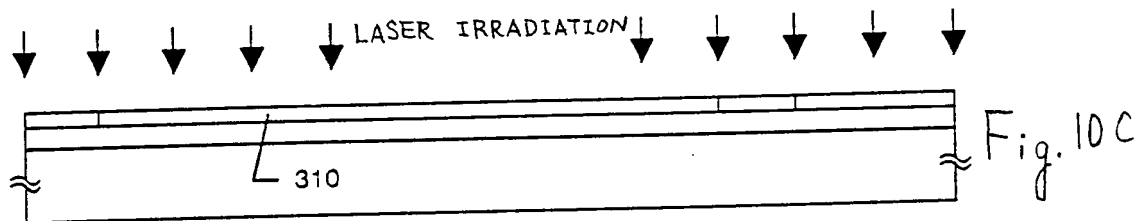
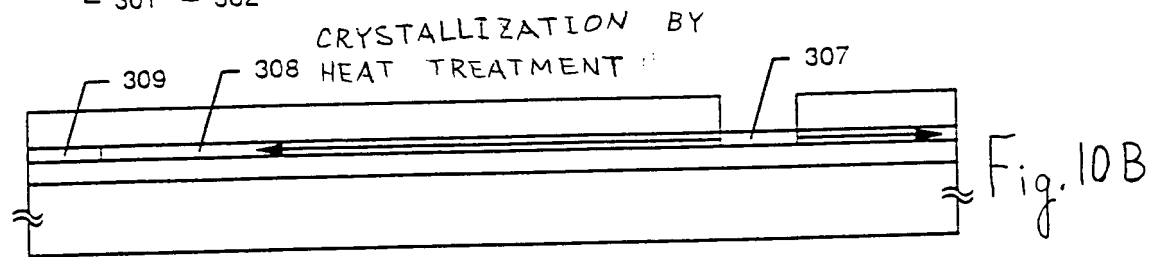
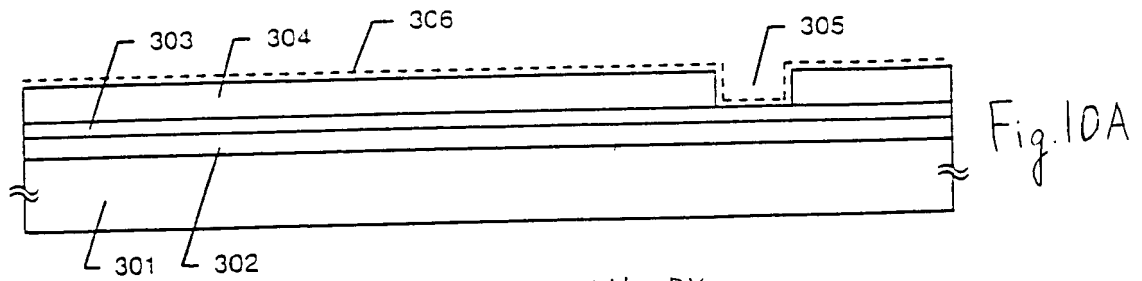
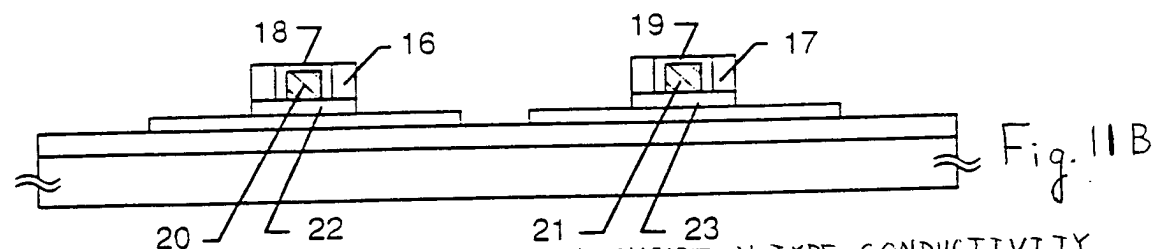
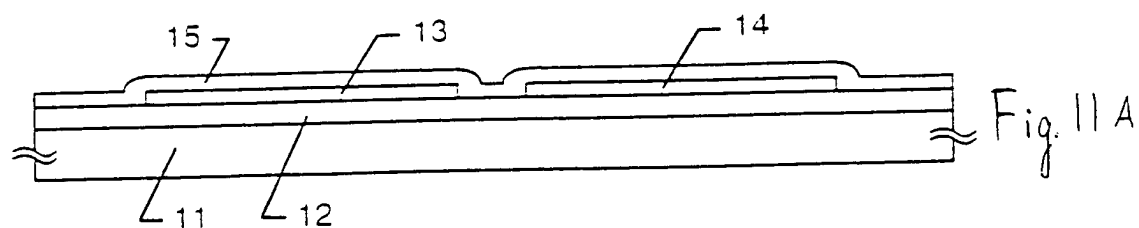
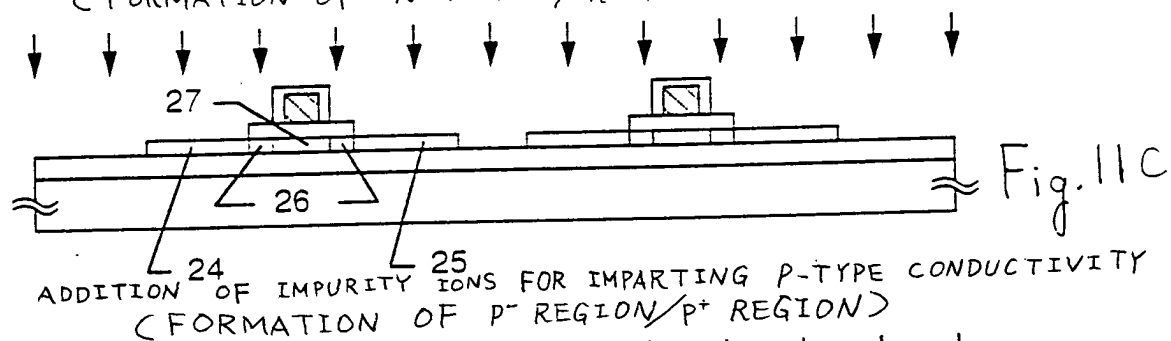


Fig. 9B

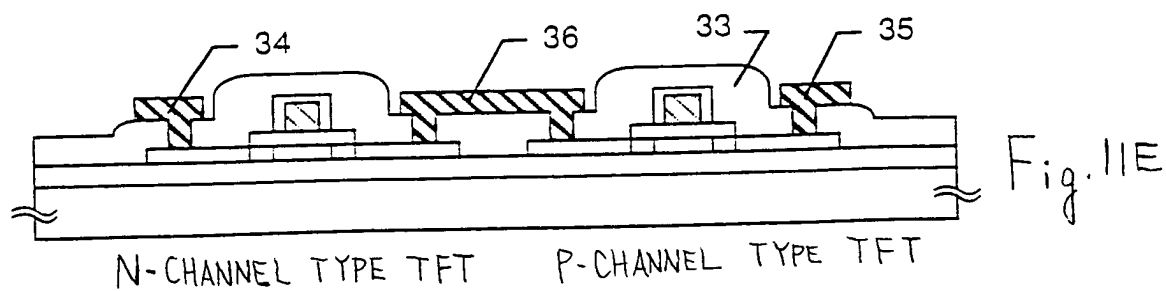
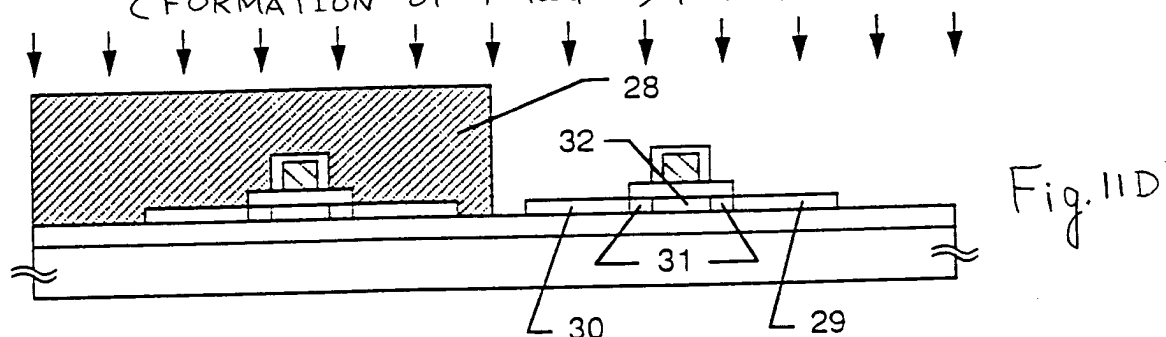




20 / L 22 21 / L 23
ADDITION OF IMPURITY IONS WHICH IMPART N-TYPE CONDUCTIVITY
(FORMATION OF n^- REGION/ n^+ REGION)



L_{24} L_{25}
 ADDITION OF IMPURITY IONS FOR IMPARTING P-TYPE CONDUCTIVITY
 (FORMATION OF P^- REGION / P^+ REGION)



N-CHANNEL TYPE TFT P-CHANNEL TYPE TFT

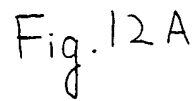
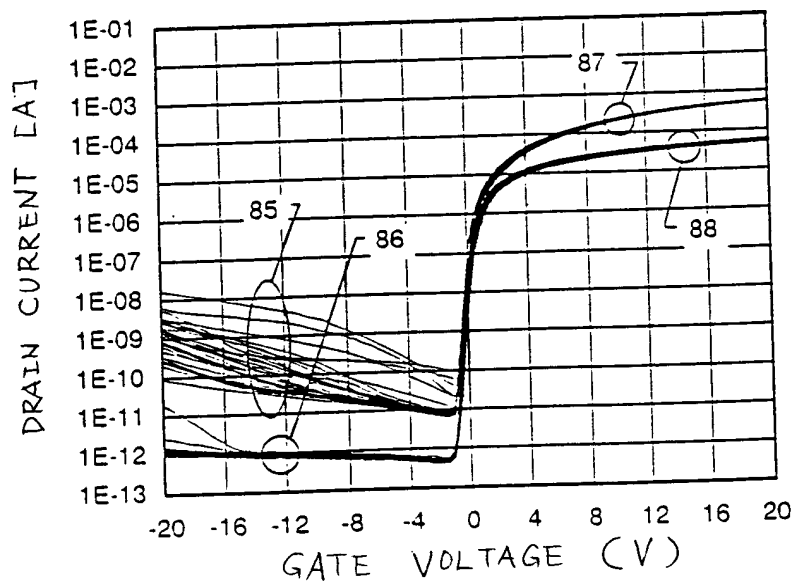
[illegible]

Fig. 12 B



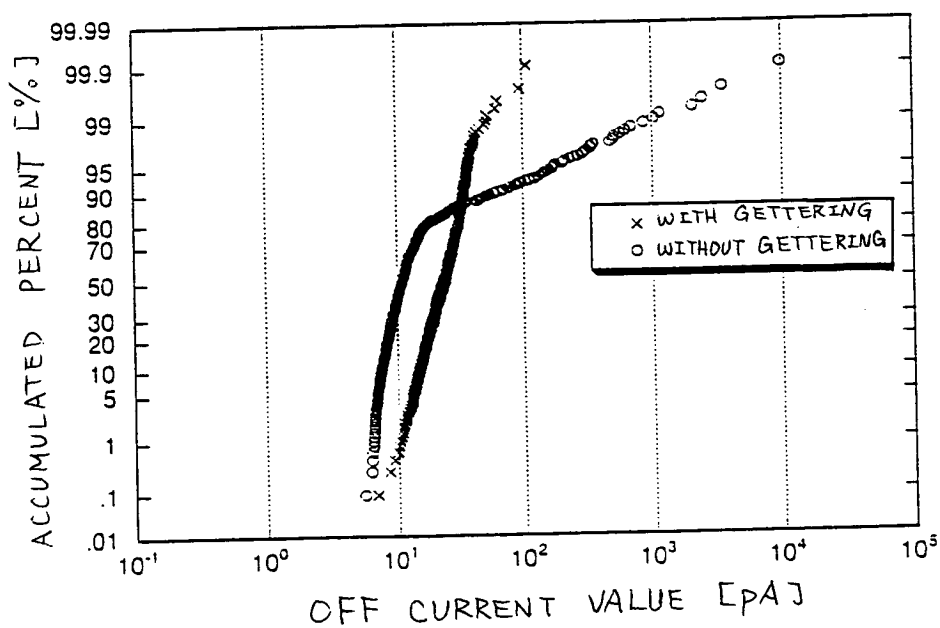
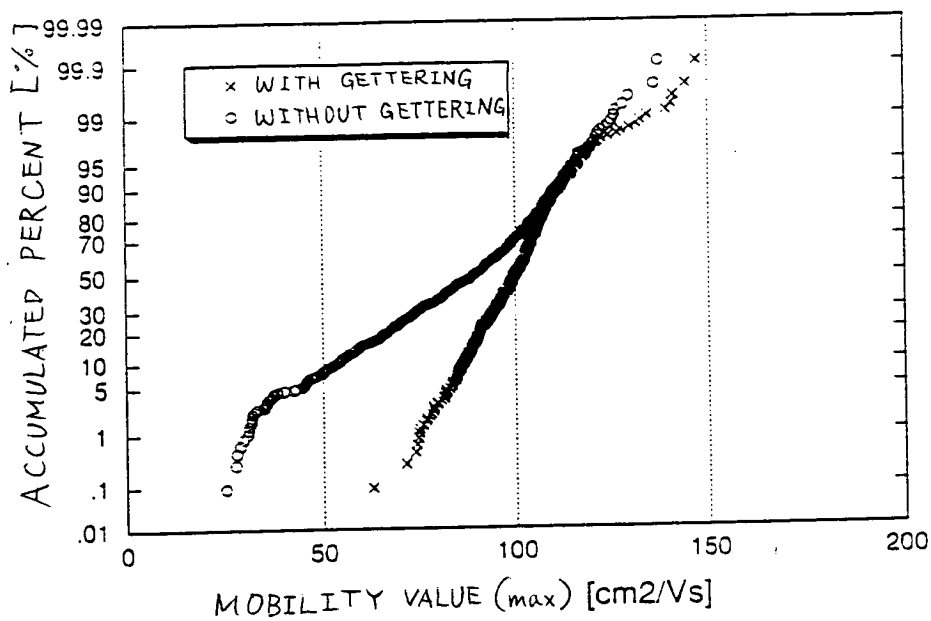
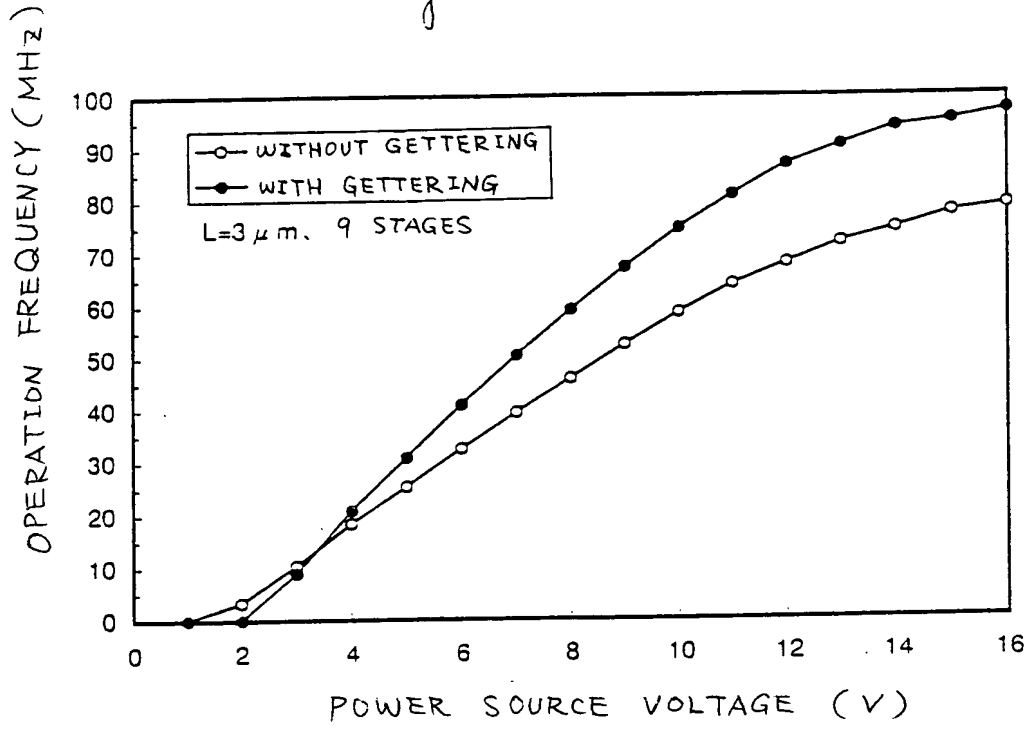
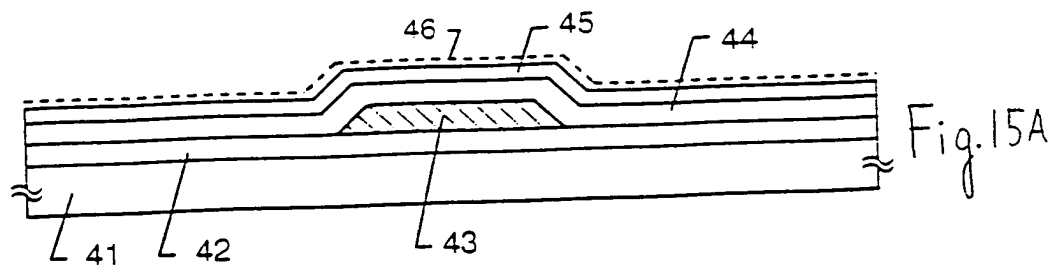


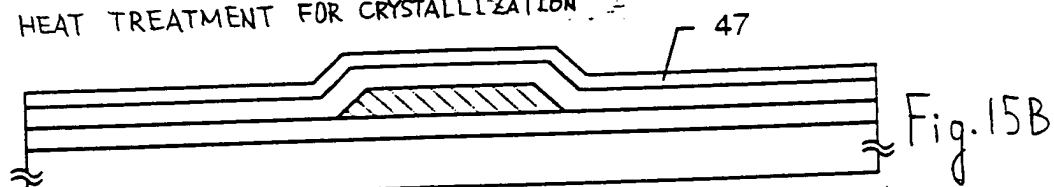
Fig. 14



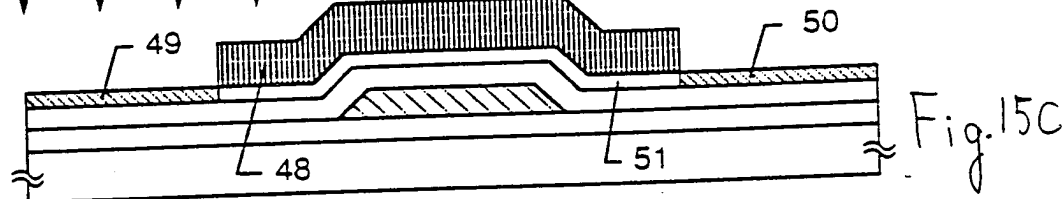
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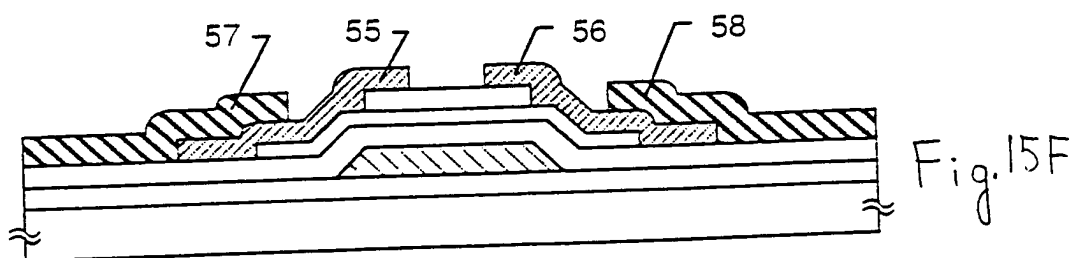
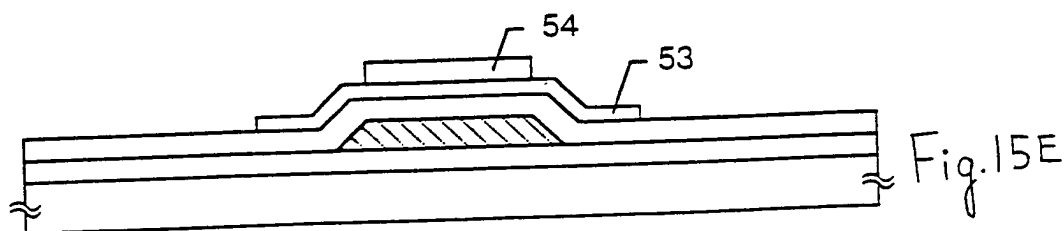
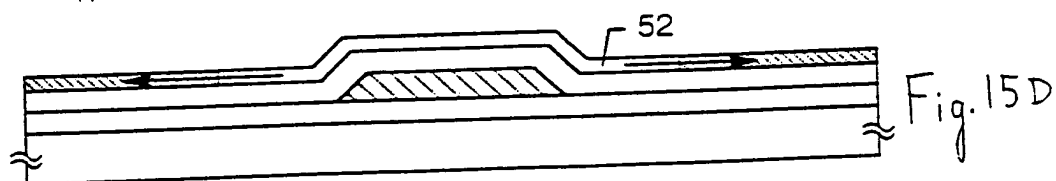
HEAT TREATMENT FOR CRYSTALLIZATION



P ION ADDITION



HEAT TREATMENT FOR GETTERING



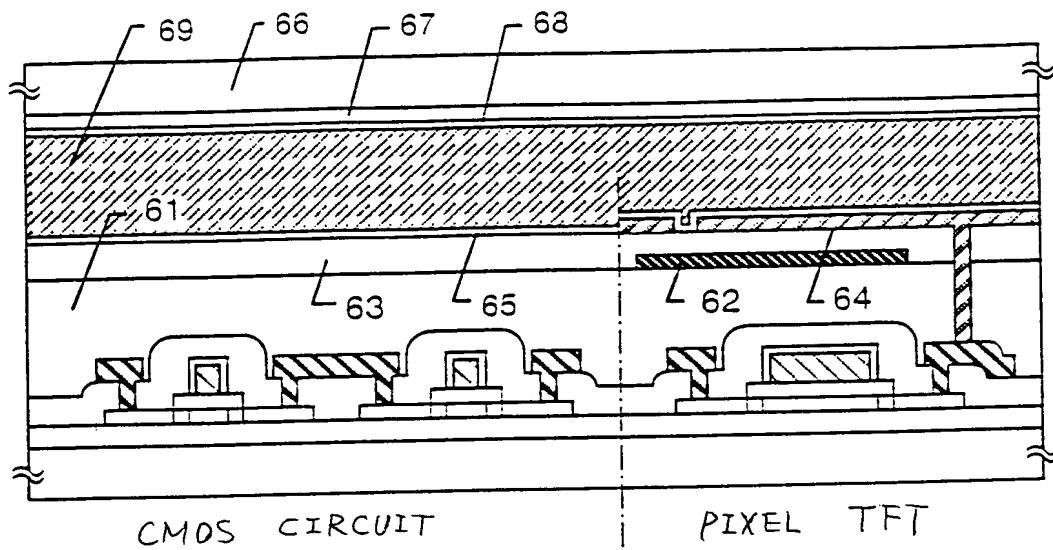


Fig. 16

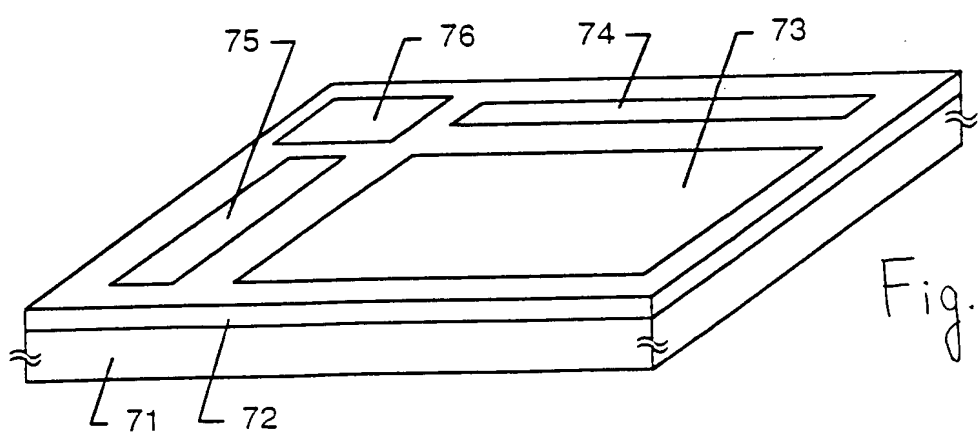


Fig. 17

